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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	516096
Number of I/O	147
Number of Gates	3000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe3000-1pq208

Temperature Grade Offerings

Package	A3PE600	A3PE1500	A3PE3000
Cortex-M1 Devices		**M1A3PE1500**	**M1A3PE3000**
PQ208	C, I	C, I	C, I
FG256	C, I	–	–
FG324	–	–	C, I
FG484	C, I	C, I	C, I
FG676	–	C, I	–
FG896	–	–	C, I

Note: C = Commercial temperature range: 0°C to 70°C ambient temperature
I = Industrial temperature range: –40°C to 85°C ambient temperature

Speed Grade and Temperature Grade Matrix

Temperature Grade	Std.	–1	–2
C [1]	✓	✓	✓
I [2]	✓	✓	✓

Notes:
1. *C = Commercial temperature range: 0°C to 70°C ambient temperature*
2. *I = Industrial temperature range: –40°C to 85°C ambient temperature*

References made to ProASIC3E devices also apply to ARM-enabled ProASIC3E devices. The ARM-enabled part numbers start with M1 (Cortex-M1).

Contact your local Microsemi SoC Products Group representative for device availability: *www.microsemi.com/index.php?option=com_content&id=135&lang=en&view=article*.

1 – ProASIC3E Device Family Overview

General Description

ProASIC3E, the third-generation family of Microsemi flash FPGAs, offers performance, density, and features beyond those of the ProASIC PLUS® family. Nonvolatile flash technology gives ProASIC3E devices the advantage of being a secure, low power, single-chip solution that is Instant On. ProASIC3E is reprogrammable and offers time-to-market benefits at an ASIC-level unit cost. These features enable designers to create high-density systems using existing ASIC or FPGA design flows and tools.

ProASIC3E devices offer 1 kbit of on-chip, programmable, nonvolatile FlashROM storage as well as clock conditioning circuitry based on six integrated phase-locked loops (PLLs). ProASIC3E devices have up to three million system gates, supported with up to 504 kbits of true dual-port SRAM and up to 620 user I/Os.

Several ProASIC3E devices support the Cortex-M1 soft IP cores, and the ARM-Enabled devices have Microsemi ordering numbers that begin with M1A3PE.

Flash Advantages

Reduced Cost of Ownership

Advantages to the designer extend beyond low unit cost, performance, and ease of use. Unlike SRAM-based FPGAs, flash-based ProASIC3E devices allow all functionality to be Instant On; no external boot PROM is required. On-board security mechanisms prevent access to all the programming information and enable secure remote updates of the FPGA logic. Designers can perform secure remote in-system reprogramming to support future design iterations and field upgrades with confidence that valuable intellectual property (IP) cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The ProASIC3E family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the ProASIC3E family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/ communications, computing, and avionics markets.

Security

The nonvolatile, flash-based ProASIC3E devices do not require a boot PROM, so there is no vulnerable external bitstream that can be easily copied. ProASIC3E devices incorporate FlashLock, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only an FPGA with nonvolatile flash programming can offer.

ProASIC3E devices utilize a 128-bit flash-based lock and a separate AES key to provide the highest level of protection in the FPGA industry for programmed intellectual property and configuration data. In addition, all FlashROM data in ProASIC3E devices can be encrypted prior to loading, using the industry-leading AES-128 (FIPS192) bit block cipher encryption standard. The AES standard was adopted by the National Institute of Standards and Technology (NIST) in 2000 and replaces the 1977 DES standard. ProASIC3E devices have a built-in AES decryption engine and a flash-based AES key that make them the most comprehensive programmable logic device security solution available today. ProASIC3E devices with AES-based security provide a high level of protection for secure, remote field updates over public networks such as the Internet, and ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves.

Security, built into the FPGA fabric, is an inherent component of the ProASIC3E family. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. The ProASIC3E family, with FlashLock and AES security, is unique in being highly resistant to both invasive and noninvasive attacks. Your valuable IP is protected with industry-standard security, making remote ISP possible. A ProASIC3E device provides the best available security for programmable logic designs.

Pro I/Os with Advanced I/O Standards

The ProASIC3E family of FPGAs features a flexible I/O structure, supporting a range of voltages (1.5 V, 1.8 V, 2.5 V, and 3.3 V). ProASIC3E FPGAs support 19 different I/O standards, including single-ended, differential, and voltage-referenced. The I/Os are organized into banks, with eight banks per device (two per side). The configuration of these banks determines the I/O standards supported. Each I/O bank is subdivided into VREF minibanks, which are used by voltage-referenced I/Os. VREF minibanks contain 8 to 18 I/Os. All the I/Os in a given minibank share a common VREF line. Therefore, if any I/O in a given VREF minibank is configured as a VREF pin, the remaining I/Os in that minibank will be able to use that reference voltage.

Each I/O module contains several input, output, and enable registers. These registers allow the implementation of the following:

- Single-Data-Rate applications (e.g., PCI 66 MHz, bidirectional SSTL 2 and 3, Class I and II)
- Double-Data-Rate applications (e.g., DDR LVDS, B-LVDS, and M-LVDS I/Os for point-to-point communications, and DDR 200 MHz SRAM using bidirectional HSTL Class II)

ProASIC3E banks support M-LVDS with 20 multi-drop points.

Hot-swap (also called hot-plug, or hot-insertion) is the operation of hot-insertion or hot-removal of a card in a powered-up system.

Cold-sparing (also called cold-swap) refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Specifying I/O States During Programming

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the *FlashPro User's Guide* for more information.

Note: PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify (Figure 1-3 on page 1-7).
5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:

   1 – I/O is set to drive out logic High

   0 – I/O is set to drive out logic Low

   Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming

   Z -Tri-State: I/O is tristated

Table 2-2 • Recommended Operating Conditions [1]

Symbol	Parameter		Commercial	Industrial	Units
T_A	Ambient temperature		0 to +70	–40 to +85	°C
T_J	Junction temperature		0 to +85	–40 to +100	°C
VCC	1.5 V DC core supply voltage		1.425 to 1.575	1.425 to 1.575	V
VJTAG	JTAG DC voltage		1.4 to 3.6	1.4 to 3.6	V
VPUMP	Programming voltage	Programming Mode[2]	3.15 to 3.45	3.15 to 3.45	V
		Operation[3]	0 to 3.6	0 to 3.6	V
VCCPLL	Analog power supply (PLL)		1.425 to 1.575	1.425 to 1.575	V
VCCI and VMV [4]	1.5 V DC supply voltage		1.425 to 1.575	1.425 to 1.575	V
	1.8 V DC supply voltage		1.7 to 1.9	1.7 to 1.9	V
	2.5 V DC supply voltage		2.3 to 2.7	2.3 to 2.7	V
	3.3 V DC supply voltage		3.0 to 3.6	3.0 to 3.6	V
	3.0 V DC supply voltage[5]		2.7 to 3.6	2.7 to 3.6	V
	LVDS/B-LVDS/M-LVDS differential I/O		2.375 to 2.625	2.375 to 2.625	V
	LVPECL differential I/O		3.0 to 3.6	3.0 to 3.6	V

Notes:

1. *All parameters representing voltages are measured with respect to GND unless otherwise specified.*
2. *The programming temperature range supported is $T_{ambient}$ = 0°C to 85°C.*
3. *VPUMP can be left floating during normal operation (not programming mode).*
4. *The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in Table 2-13 on page 2-16. VMV and VCCI should be at the same voltage within a given I/O bank. VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information.*
5. *To ensure targeted reliability standards are met across ambient and junction operating temperatures, Microsemi recommends that the user follow best design practices using Microsemi's timing and power simulation tools.*
6. *3.3 V wide range is compliant to the JESD8-B specification and supports 3.0 V VCCI operation.*

Table 2-3 • Flash Programming Limits – Retention, Storage and Operating Temperature [1]

Product Grade	Programming Cycles	Program Retention (biased/unbiased)	Maximum Storage Temperature T_{STG} (°C) [2]	Maximum Operating Junction Temperature T_J (°C) [2]
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

Notes:

1. *This is a stress rating only; functional operation at any condition other than those indicated is not implied.*
2. *These limits apply for program/data retention only. Refer to Table 2-1 on page 2-1 and Table 2-2 for device operating conditions and absolute limits.*

Guidelines

Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that this net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100% as all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
  - Bit 0 (LSB) = 100%
  - Bit 1 = 50%
  - Bit 2 = 25%
  - …
  - Bit 7 (MSB) = 0.78125%
  - Average toggle rate = (100% + 50% + 25% + 12.5% + . . . + 0.78125%) / 8

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

***Table 2-11* • Toggle Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

***Table 2-12* • Enable Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%

User I/O Characteristics

Timing Model

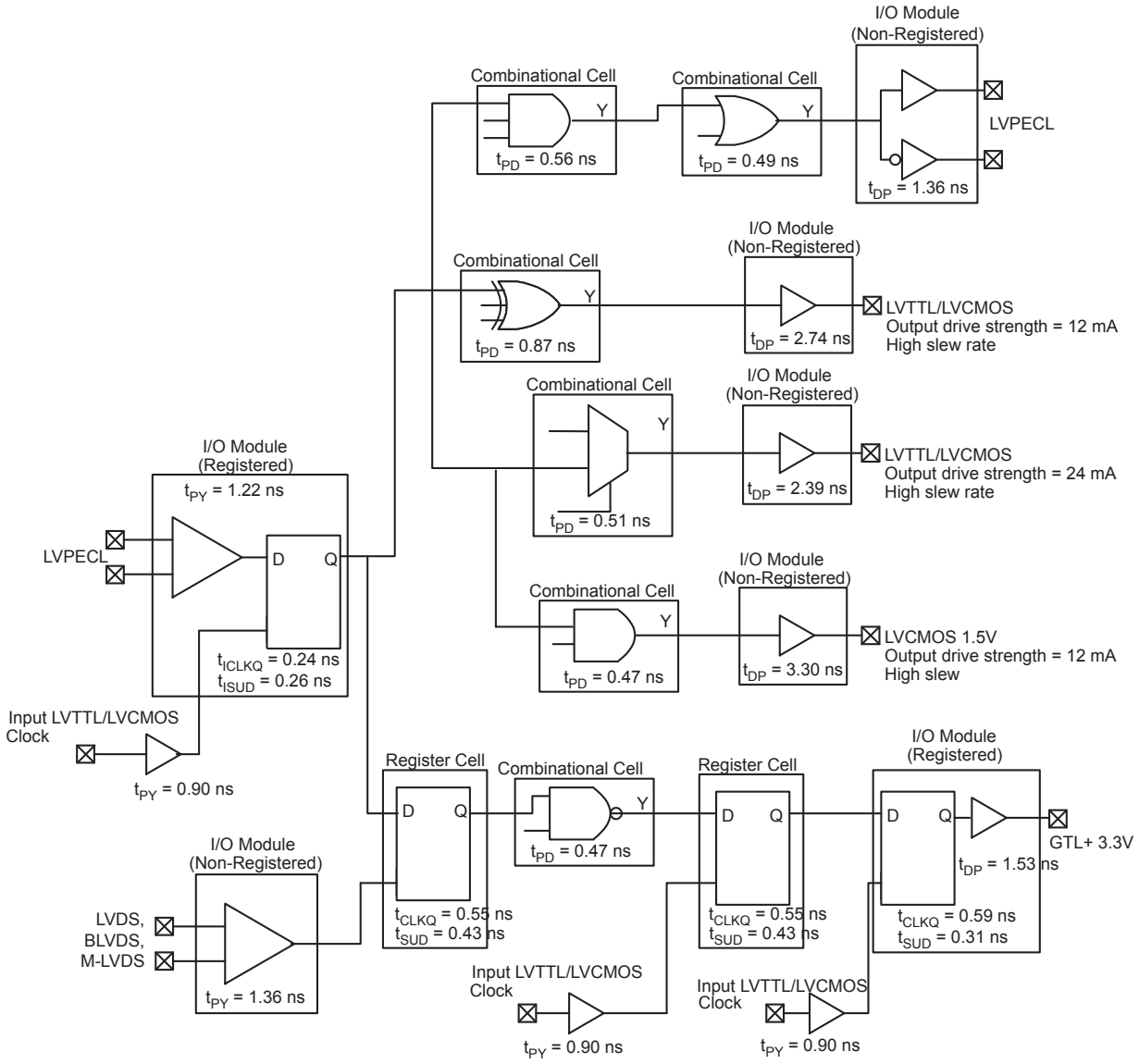


Figure 2-2 • **Timing Model**
Operating Conditions: –2 Speed, Commercial Temperature Range (T_J = 70°C), Worst-Case VCC = 1.425 V

Table 2-19 • I/O Output Buffer Maximum Resistances[1] (continued)

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω)[2]	$R_{PULL\text{-}UP}$ (Ω)[3]
3.3 V GTL+	35 mA	12	–
2.5 V GTL+	33 mA	15	–
HSTL (I)	8 mA	50	50
HSTL (II)	15 mA[4]	25	25
SSTL2 (I)	15 mA	27	31
SSTL2 (II)	18 mA	13	15
SSTL3 (I)	14 mA	44	69
SSTL3 (II)	21 mA	18	32

Notes:

1. *These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website at www.microsemi.com/index.php?option=com_content&id=1671&lang=en&view=article.*
2. $R_{(PULL\text{-}DOWN\text{-}MAX)}$ = (VOLspec) / IOLspec
3. $R_{(PULL\text{-}UP\text{-}MAX)}$ = (VCCImax – VOHspec) / IOHspec
4. *Output drive strength is below JEDEC specification.*

Table 2-20 • I/O Weak Pull-Up/Pull-Down Resistances
Minimum and Maximum Weak Pull-Up/Pull-Down Resistance Values

	$R_{(WEAK\ PULL\text{-}UP)}$[1] (Ω)		$R_{(WEAK\ PULL\text{-}DOWN)}$[2] (Ω)	
VCCI	Min.	Max.	Min.	Max.
3.3 V	10 k	45 k	10 k	45 k
3.3 V (Wide Range I/Os)	10 k	45 k	10 k	45 k
2.5 V	11 k	55 k	12 k	74 k
1.8 V	18 k	70 k	17 k	110 k
1.5 V	19 k	90 k	19 k	140 k

Notes:

1. $R_{(WEAK\ PULL\text{-}UP\text{-}MAX)}$ = (VCCImax – VOHspec) / $I_{(WEAK\ PULL\text{-}UP\text{-}MIN)}$
2. $R_{(WEAK\ PULL\text{-}DOWN\text{-}MAX)}$ = (VOLspec) / $I_{(WEAK\ PULL\text{-}DOWN\text{-}MIN)}$

Timing Characteristics

Table 2-43 • 1.5 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	8.53	0.04	1.70	2.14	0.43	7.26	8.53	3.39	2.79	9.50	10.77	ns
	–1	0.56	7.26	0.04	1.44	1.82	0.36	6.18	7.26	2.89	2.37	8.08	9.16	ns
	–2	0.49	6.37	0.03	1.27	1.60	0.32	5.42	6.37	2.53	2.08	7.09	8.04	ns
4 mA	Std.	0.66	5.41	0.04	1.70	2.14	0.43	5.22	5.41	3.75	3.48	7.45	7.65	ns
	–1	0.56	4.60	0.04	1.44	1.82	0.36	4.44	4.60	3.19	2.96	6.34	6.50	ns
	–2	0.49	4.04	0.03	1.27	1.60	0.32	3.89	4.04	2.80	2.60	5.56	5.71	ns
6 mA	Std.	0.66	4.80	0.04	1.70	2.14	0.43	4.89	4.75	3.83	3.67	7.13	6.98	ns
	–1	0.56	4.09	0.04	1.44	1.82	0.36	4.16	4.04	3.26	3.12	6.06	5.94	ns
	–2	0.49	3.59	0.03	1.27	1.60	0.32	3.65	3.54	2.86	2.74	5.32	5.21	ns
8 mA	Std.	0.66	4.42	0.04	1.70	2.14	0.43	4.50	3.62	3.96	4.37	6.74	5.86	ns
	–1	0.56	3.76	0.04	1.44	1.82	0.36	3.83	3.08	3.37	3.72	5.73	4.98	ns
	–2	0.49	3.30	0.03	1.27	1.60	0.32	3.36	2.70	2.96	3.27	5.03	4.37	ns
12 mA	Std.	0.66	4.42	0.04	1.70	2.14	0.43	4.50	3.62	3.96	4.37	6.74	5.86	ns
	–1	0.56	3.76	0.04	1.44	1.82	0.36	3.83	3.08	3.37	3.72	5.73	4.98	ns
	–2	0.49	3.30	0.03	1.27	1.60	0.32	3.36	2.70	2.96	3.27	5.03	4.37	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

Table 2-44 • 1.5 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	14.11	0.04	1.70	2.14	0.43	14.37	13.14	3.40	2.68	16.61	15.37	ns
	–1	0.56	12.00	0.04	1.44	1.82	0.36	12.22	11.17	2.90	2.28	14.13	13.08	ns
	–2	0.49	10.54	0.03	1.27	1.60	0.32	10.73	9.81	2.54	2.00	12.40	11.48	ns
4 mA	Std.	0.66	11.23	0.04	1.70	2.14	0.43	11.44	9.87	3.77	3.36	13.68	12.10	ns
	–1	0.56	9.55	0.04	1.44	1.82	0.36	9.73	8.39	3.21	2.86	11.63	10.29	ns
	–2	0.49	8.39	0.03	1.27	1.60	0.32	8.54	7.37	2.81	2.51	10.21	9.04	ns
6 mA	Std.	0.66	10.45	0.04	1.70	2.14	0.43	10.65	9.24	3.84	3.55	12.88	11.48	ns
	–1	0.56	8.89	0.04	1.44	1.82	0.36	9.06	7.86	3.27	3.02	10.96	9.76	ns
	–2	0.49	7.81	0.03	1.27	1.60	0.32	7.95	6.90	2.87	2.65	9.62	8.57	ns
8 mA	Std.	0.66	10.02	0.04	1.70	2.14	0.43	10.20	9.23	3.97	4.22	12.44	11.47	ns
	–1	0.56	8.52	0.04	1.44	1.82	0.36	8.68	7.85	3.38	3.59	10.58	9.75	ns
	–2	0.49	7.48	0.03	1.27	1.60	0.32	7.62	6.89	2.97	3.15	9.29	8.56	ns
12 mA	Std.	0.66	10.02	0.04	1.70	2.14	0.43	10.20	9.23	3.97	4.22	12.44	11.47	ns
	–1	0.56	8.52	0.04	1.44	1.82	0.36	8.68	7.85	3.38	3.59	10.58	9.75	ns
	–2	0.49	7.48	0.03	1.27	1.60	0.32	7.62	6.89	2.97	3.15	9.29	8.56	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

SSTL2 Class II

Stub-Speed Terminated Logic for 2.5 V memory bus standard (JESD8-9). ProASIC3E devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-69 • Minimum and Maximum DC Input and Output Levels

SSTL2 Class II	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
18 mA	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.35	VCCI – 0.43	18	18	124	169	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*

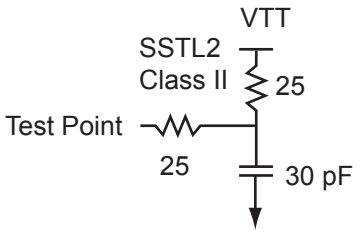


Figure 2-19 • AC Loading

Table 2-70 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.2	VREF + 0.2	1.25	1.25	1.25	30

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-71 • SSTL 2 Class II
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V, VREF = 1.25 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.66	0.66	2.17	0.04	1.33	0.43	2.21	1.77			4.44	ns
–1	0.56	0.56	1.84	0.04	1.14	0.36	1.88	1.51			3.78	ns
–2	0.49	0.49	1.62	0.03	1.00	0.32	1.65	1.32			3.32	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Timing Characteristics

Table 2-80 • LVDS
Commercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.66	1.87	0.04	1.82	ns
–1	0.56	1.59	0.04	1.55	ns
–2	0.49	1.40	0.03	1.36	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

B-LVDS/M-LVDS

Bus LVDS (B-LVDS) and Multipoint LVDS (M-LVDS) specifications extend the existing LVDS standard to high-performance multipoint bus applications. Multidrop and multipoint bus configurations may contain any combination of drivers, receivers, and transceivers. Microsemi LVDS drivers provide the higher drive current required by B-LVDS and M-LVDS to accommodate the loading. The drivers require series terminations for better signal quality and to control voltage swing. Termination is also required at both ends of the bus since the driver can be located anywhere on the bus. These configurations can be implemented using the TRIBUF_LVDS and BIBUF_LVDS macros along with appropriate terminations. Multipoint designs using Microsemi LVDS macros can achieve up to 200 MHz with a maximum of 20 loads. A sample application is given in Figure 2-23. The input and output buffer delays are available in the LVDS section in Table 2-80.

Example: For a bus consisting of 20 equidistant loads, the following terminations provide the required differential voltage, in worst-case Industrial operating conditions, at the farthest receiver: R_S = 60 Ω and R_T = 70 Ω, given Z_0 = 50 Ω (2") and Z_{stub} = 50 Ω (~1.5").

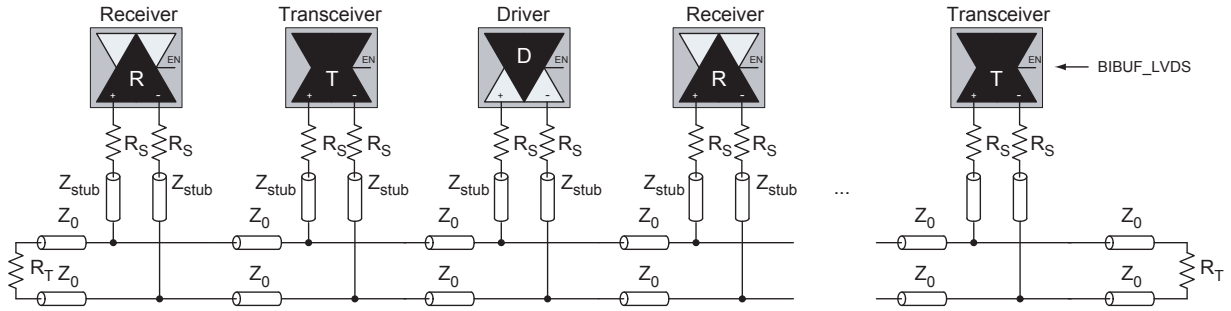


Figure 2-23 • B-LVDS/M-LVDS Multipoint Application Using LVDS I/O Buffers

DDR Module Specifications

Input DDR Module

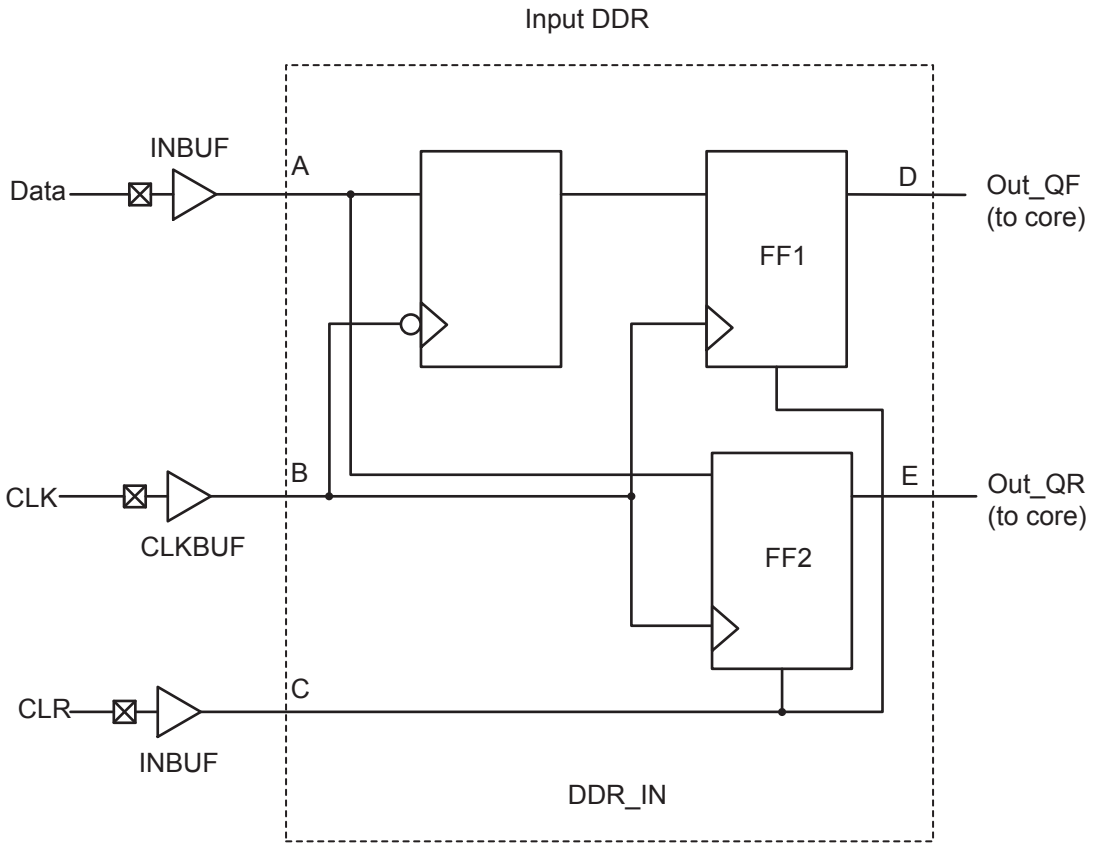
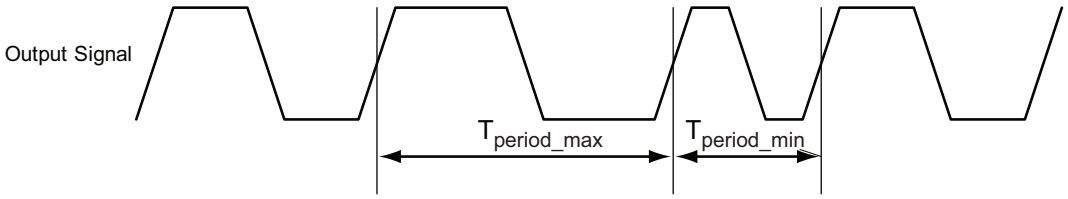


Figure 2-30 • **Input DDR Timing Model**

Table 2-89 • **Parameter Definitions**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR	B, D
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF	B, E
$t_{DDRISUD}$	Data Setup Time of DDR input	A, B
t_{DDRIHD}	Data Hold Time of DDR input	A, B
$t_{DDRICLR2Q1}$	Clear-to-Out Out_QR	C, D
$t_{DDRICLR2Q2}$	Clear-to-Out Out_QF	C, E
$t_{DDRIREMCLR}$	Clear Removal	C, B
$t_{DDRIRECCLR}$	Clear Recovery	C, B



Note: Peak-to-peak jitter measurements are defined by $T_{peak\text{-}to\text{-}peak} = T_{period\_max} - T_{period\_min}$.

Figure 2-39 • **Peak-to-Peak Jitter Definition**

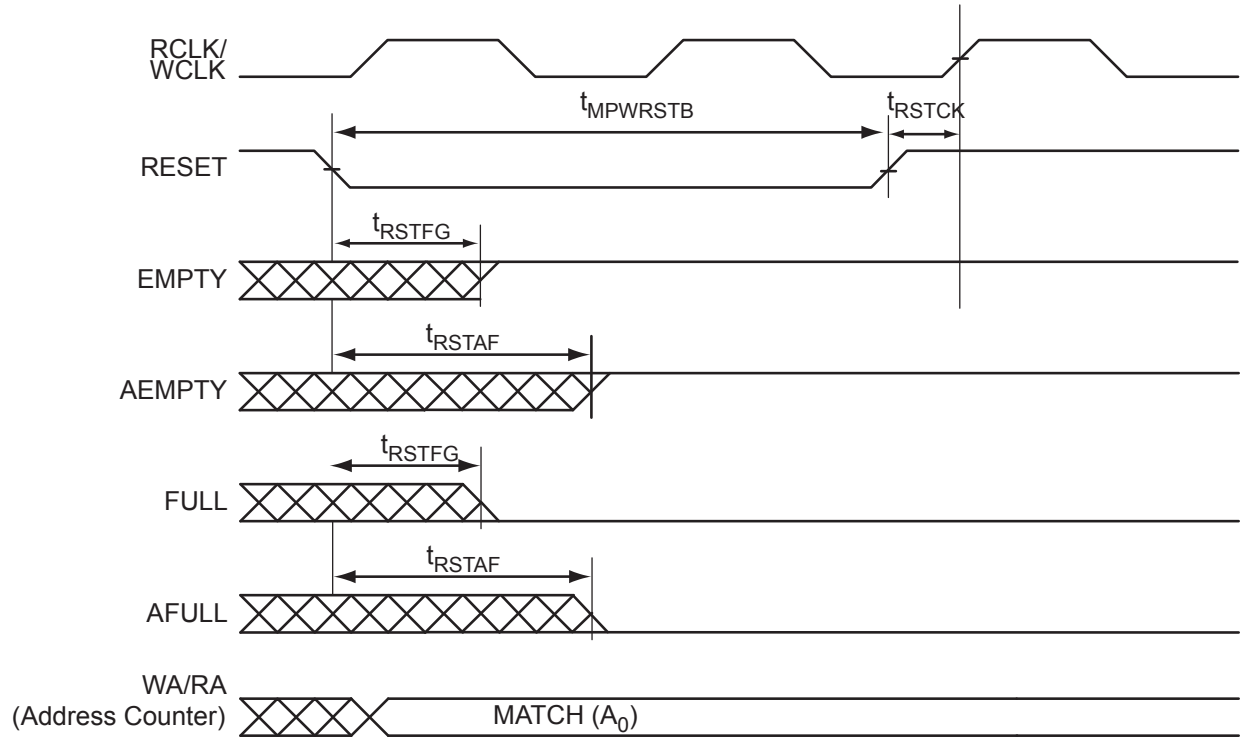


Figure 2-49 • **FIFO Reset**

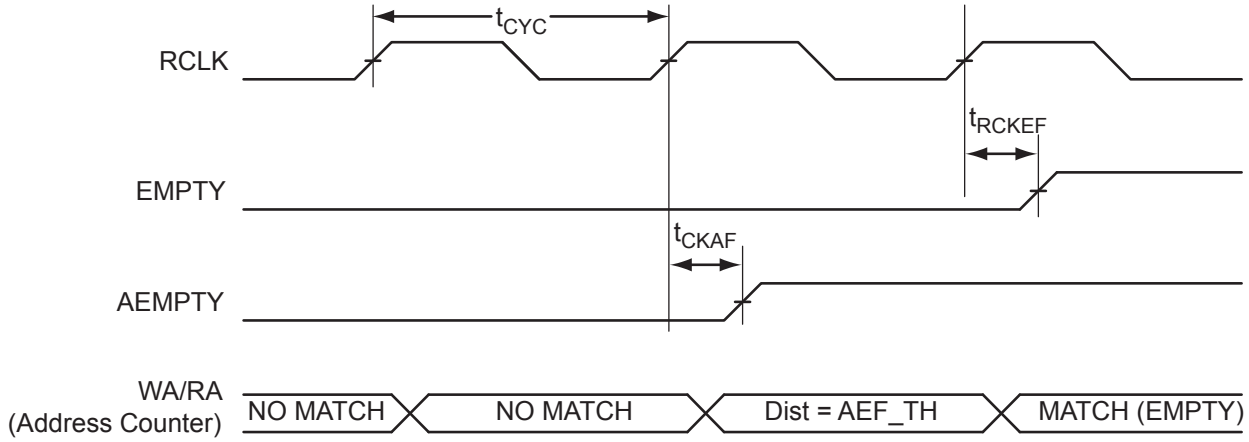


Figure 2-50 • **FIFO EMPTY Flag and AEMPTY Flag Assertion**

3 – Pin Descriptions and Packaging

Supply Pins

GND **Ground**

Ground supply voltage to the core, I/O outputs, and I/O logic.

GNDQ **Ground (quiet)**

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ must always be connected to GND on the board.

VCC **Core Supply Voltage**

Supply voltage to the FPGA core, nominally 1.5 V. VCC is required for powering the JTAG state machine in addition to VJTAG. Even when a device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the device.

VCCIBx **I/O Supply Voltage**

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are up to eight I/O banks on low power flash devices plus a dedicated VJTAG bank. Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCIBx supply. VCCI can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. In general, unused I/O banks should have their corresponding VCCIX pins tied to GND. If an output pad is terminated to ground through any resistor and if the corresponding VCCIX is left floating, then the leakage current to ground is ~ 0uA. However, if an output pad is terminated to ground through any resistor and the corresponding VCCIX grounded, then the leakage current to ground is ~ 3 uA. For unused banks the aforementioned behavior is to be taken into account while deciding if it’s better to float VCCIX of unused bank or tie it to GND.

VMVx **I/O Supply Voltage (quiet)**

Quiet supply voltage to the input buffers of each I/O bank. *x* is the bank number. Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks. This minimizes the noise transfer within the package and improves input signal integrity. Each bank must have at least one VMV connection, and no VMV should be left unconnected. All I/Os in a bank run off the same VMVx supply. VMV is used to provide a quiet supply voltage to the input buffers of each I/O bank. VMVx can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VMV pins tied to GND. VMV and VCCI should be at the same voltage within a given I/O bank. Used VMV pins must be connected to the corresponding VCCI pins of the same bank (i.e., VMV0 to VCCIB0, VMV1 to VCCIB1, etc.).

VCCPLA/B/C/D/E/F **PLL Supply Voltage**

Supply voltage to analog PLL, nominally 1.5 V.

When the PLLs are not used, the place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Microsemi recommends tying VCCPLx to VCC and using proper filtering circuits to decouple VCC noise from the PLLs. Refer to the PLL Power Supply Decoupling section of the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" chapter of the *ProASIC3E FPGA Fabric User’s Guide* for a complete board solution for the PLL analog power supply and ground.

There are six VCCPLX pins on ProASIC3E devices.

VCOMPLA/B/C/D/E/F **PLL Ground**

Ground to analog PLL power supplies. When the PLLs are not used, the place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground.

There are six VCOMPL pins (PLL ground) on ProASIC3E devices.

FG484	
Pin Number	**A3PE600 Function**
C21	NC
C22	VCCIB2
D1	NC
D2	NC
D3	NC
D4	GND
D5	GAA0/IO00NDB0V0
D6	GAA1/IO00PDB0V0
D7	GAB0/IO01NDB0V0
D8	IO05PDB0V0
D9	IO10PDB0V1
D10	IO12PDB0V2
D11	IO16NDB0V2
D12	IO23NDB1V0
D13	IO23PDB1V0
D14	IO28NDB1V1
D15	IO28PDB1V1
D16	GBB1/IO34PDB1V1
D17	GBA0/IO35NDB1V1
D18	GBA1/IO35PDB1V1
D19	GND
D20	NC
D21	NC
D22	NC
E1	NC
E2	NC
E3	GND
E4	GAB2/IO133PDB7V1
E5	GAA2/IO134PDB7V1
E6	GNDQ
E7	GAB1/IO01PDB0V0
E8	IO05NDB0V0
E9	IO10NDB0V1
E10	IO12NDB0V2
E11	IO16PDB0V2
E12	IO20NDB1V0

FG484	
Pin Number	**A3PE600 Function**
E13	IO24NDB1V0
E14	IO24PDB1V0
E15	GBC1/IO33PDB1V1
E16	GBB0/IO34NDB1V1
E17	GNDQ
E18	GBA2/IO36PDB2V0
E19	IO42NDB2V0
E20	GND
E21	NC
E22	NC
F1	NC
F2	IO131NDB7V1
F3	IO131PDB7V1
F4	IO133NDB7V1
F5	IO134NDB7V1
F6	VMV7
F7	VCCPLA
F8	GAC0/IO02NDB0V0
F9	GAC1/IO02PDB0V0
F10	IO15NDB0V2
F11	IO15PDB0V2
F12	IO20PDB1V0
F13	IO25NDB1V0
F14	IO27PDB1V0
F15	GBC0/IO33NDB1V1
F16	VCCPLB
F17	VMV2
F18	IO36NDB2V0
F19	IO42PDB2V0
F20	NC
F21	NC
F22	NC
G1	IO127NDB7V1
G2	IO127PDB7V1
G3	NC
G4	IO128PDB7V1

FG484	
Pin Number	**A3PE600 Function**
G5	IO129PDB7V1
G6	GAC2/IO132PDB7V1
G7	VCOMPLA
G8	GNDQ
G9	IO09NDB0V1
G10	IO09PDB0V1
G11	IO13PDB0V2
G12	IO21PDB1V0
G13	IO25PDB1V0
G14	IO27NDB1V0
G15	GNDQ
G16	VCOMPLB
G17	GBB2/IO37PDB2V0
G18	IO39PDB2V0
G19	IO39NDB2V0
G20	IO43PDB2V0
G21	IO43NDB2V0
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO128NDB7V1
H5	IO129NDB7V1
H6	IO132NDB7V1
H7	IO130PDB7V1
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO13NDB0V2
H12	IO21NDB1V0
H13	VCCIB1
H14	VCCIB1
H15	VMV1
H16	GBC2/IO38PDB2V0
H17	IO37NDB2V0
H18	IO41NDB2V0

FG484	
Pin Number	A3PE1500 Function
N17	IO91NPB3V0
N18	IO90NPB3V0
N19	IO91PPB3V0
N20	GNDQ
N21	IO93NDB3V0
N22	IO95PDB3V1
P1	NC
P2	IO183PDB6V2
P3	IO187NPB6V2
P4	IO184NPB6V2
P5	IO176PPB6V1
P6	IO182PDB6V1
P7	IO182NDB6V1
P8	VCCIB6
P9	GND
P10	VCC
P11	VCC
P12	VCC
P13	VCC
P14	GND
P15	VCCIB3
P16	GDB0/IO109NPB3V2
P17	IO97NDB3V1
P18	IO97PDB3V1
P19	IO99PDB3V1
P20	VMV3
P21	IO98PDB3V1
P22	IO95NDB3V1
R1	NC
R2	IO177PDB6V1
R3	VCC
R4	IO176NPB6V1
R5	IO174NDB6V0
R6	IO174PDB6V0
R7	GEC0/IO169NPB6V0
R8	VMV5

FG484	
Pin Number	A3PE1500 Function
R9	VCCIB5
R10	VCCIB5
R11	IO135NDB5V0
R12	IO135PDB5V0
R13	VCCIB4
R14	VCCIB4
R15	VMV3
R16	VCCPLD
R17	GDB1/IO109PPB3V2
R18	GDC1/IO108PDB3V2
R19	IO99NDB3V1
R20	VCC
R21	IO98NDB3V1
R22	IO101PDB3V1
T1	NC
T2	IO177NDB6V1
T3	NC
T4	IO171PDB6V0
T5	IO171NDB6V0
T6	GEC1/IO169PPB6V0
T7	VCOMPLE
T8	GNDQ
T9	GEA2/IO166PPB5V3
T10	IO145NDB5V1
T11	IO141NDB5V0
T12	IO139NDB5V0
T13	IO119NDB4V1
T14	IO119PDB4V1
T15	GNDQ
T16	VCOMPLD
T17	VJTAG
T18	GDC0/IO108NDB3V2
T19	GDA1/IO110PDB3V2
T20	NC
T21	IO103PDB3V2
T22	IO101NDB3V1

FG484	
Pin Number	A3PE1500 Function
U1	IO175PPB6V1
U2	IO173PDB6V0
U3	IO173NDB6V0
U4	GEB1/IO168PDB6V0
U5	GEB0/IO168NDB6V0
U6	VMV6
U7	VCCPLE
U8	IO166NPB5V3
U9	IO157PPB5V2
U10	IO145PDB5V1
U11	IO141PDB5V0
U12	IO139PDB5V0
U13	IO121NDB4V1
U14	IO121PDB4V1
U15	VMV4
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO110NDB3V2
U20	NC
U21	IO103NDB3V2
U22	IO105PDB3V2
V1	NC
V2	IO175NPB6V1
V3	GND
V4	GEA1/IO167PDB6V0
V5	GEA0/IO167NDB6V0
V6	GNDQ
V7	GEC2/IO164PDB5V3
V8	IO157NPB5V2
V9	IO151NDB5V2
V10	IO151PDB5V2
V11	IO137NDB5V0
V12	IO137PDB5V0
V13	IO123NDB4V1
V14	IO123PDB4V1

FG676	
Pin Number	A3PE1500 Function
R21	IO89NDB3V0
R22	GCB2/IO89PDB3V0
R23	IO90NDB3V0
R24	GCC2/IO90PDB3V0
R25	IO91PDB3V0
R26	IO91NDB3V0
T1	IO186PDB6V2
T2	IO185NDB6V2
T3	GNDQ
T4	IO180PDB6V1
T5	IO180NDB6V1
T6	IO188NDB6V2
T7	GFB2/IO188PDB6V2
T8	VCCIB6
T9	VCC
T10	GND
T11	GND
T12	GND
T13	GND
T14	GND
T15	GND
T16	GND
T17	GND
T18	VCC
T19	VCCIB3
T20	IO99PDB3V1
T21	IO99NDB3V1
T22	IO97PDB3V1
T23	IO97NDB3V1
T24	GNDQ
T25	IO93PPB3V0
T26	NC
U1	IO186NDB6V2
U2	IO184NDB6V2
U3	IO184PDB6V2
U4	IO182NDB6V1

FG676	
Pin Number	A3PE1500 Function
U5	IO182PDB6V1
U6	IO178PDB6V1
U7	IO178NDB6V1
U8	VCCIB6
U9	VCC
U10	GND
U11	GND
U12	GND
U13	GND
U14	GND
U15	GND
U16	GND
U17	GND
U18	VCC
U19	VCCIB3
U20	NC
U21	IO101NDB3V1
U22	IO101PDB3V1
U23	IO92NDB3V0
U24	IO92PDB3V0
U25	IO95PDB3V1
U26	IO93NPB3V0
V1	IO183PDB6V2
V2	IO183NDB6V2
V3	VMV6
V4	IO181PDB6V1
V5	IO181NDB6V1
V6	IO176PDB6V1
V7	IO176NDB6V1
V8	VCCIB6
V9	VCC
V10	VCC
V11	VCC
V12	VCC
V13	VCC
V14	VCC

FG676	
Pin Number	A3PE1500 Function
V15	VCC
V16	VCC
V17	VCC
V18	VCC
V19	VCCIB3
V20	IO107PDB3V2
V21	IO107NDB3V2
V22	IO103NDB3V2
V23	IO103PDB3V2
V24	VMV3
V25	IO95NDB3V1
V26	IO94PDB3V0
W1	IO179NDB6V1
W2	IO179PDB6V1
W3	IO177NDB6V1
W4	IO177PDB6V1
W5	IO172PDB6V0
W6	IO172NDB6V0
W7	VCC
W8	VCC
W9	VCCIB5
W10	VCCIB5
W11	VCCIB5
W12	VCCIB5
W13	VCCIB5
W14	VCCIB4
W15	VCCIB4
W16	VCCIB4
W17	VCCIB4
W18	VCCIB4
W19	VCC
W20	VCCIB3
W21	GDB0/IO109NDB3V2
W22	GDB1/IO109PDB3V2
W23	IO105NDB3V2
W24	IO105PDB3V2

FG896	
Pin Number	A3PE3000 Function
E17	IO49PDB1V1
E18	IO50PDB1V1
E19	IO58PDB1V2
E20	IO60NDB1V2
E21	IO77PDB1V4
E22	IO68NDB1V3
E23	IO68PDB1V3
E24	VCCIB1
E25	IO74PDB1V4
E26	VCC
E27	GBB1/IO80PPB1V4
E28	VCCIB2
E29	IO82NPB2V0
E30	GND
F1	IO296PPB7V2
F2	VCC
F3	IO306PDB7V4
F4	IO297PDB7V2
F5	VMV7
F6	GND
F7	GNDQ
F8	IO12NDB0V1
F9	IO12PDB0V1
F10	IO10PDB0V1
F11	IO16PDB0V1
F12	IO22NDB0V2
F13	IO30NDB0V3
F14	IO30PDB0V3
F15	IO36PDB0V4
F16	IO48NDB1V0
F17	IO48PDB1V0
F18	IO50NDB1V1
F19	IO58NDB1V2
F20	IO60PDB1V2
F21	IO77NDB1V4
F22	IO72NDB1V3

FG896	
Pin Number	A3PE3000 Function
F23	IO72PDB1V3
F24	GNDQ
F25	GND
F26	VMV2
F27	IO86PDB2V0
F28	IO92PDB2V1
F29	VCC
F30	IO100NPB2V2
G1	GND
G2	IO296NPB7V2
G3	IO306NDB7V4
G4	IO297NDB7V2
G5	VCCIB7
G6	GNDQ
G7	VCC
G8	VMV0
G9	VCCIB0
G10	IO10NDB0V1
G11	IO16NDB0V1
G12	IO22PDB0V2
G13	IO26PPB0V3
G14	IO38NPB0V4
G15	IO36NDB0V4
G16	IO46NDB1V0
G17	IO46PDB1V0
G18	IO56NDB1V1
G19	IO56PDB1V1
G20	IO66NDB1V3
G21	IO66PDB1V3
G22	VCCIB1
G23	VMV1
G24	VCC
G25	GNDQ
G26	VCCIB2
G27	IO86NDB2V0
G28	IO92NDB2V1

FG896	
Pin Number	A3PE3000 Function
G29	IO100PPB2V2
G30	GND
H1	IO294PDB7V2
H2	IO294NDB7V2
H3	IO300NDB7V3
H4	IO300PDB7V3
H5	IO295PDB7V2
H6	IO299PDB7V3
H7	VCOMPLA
H8	GND
H9	IO08NDB0V0
H10	IO08PDB0V0
H11	IO18PDB0V2
H12	IO26NPB0V3
H13	IO28NDB0V3
H14	IO28PDB0V3
H15	IO38PPB0V4
H16	IO42NDB1V0
H17	IO52NDB1V1
H18	IO52PDB1V1
H19	IO62NDB1V2
H20	IO62PDB1V2
H21	IO70NDB1V3
H22	IO70PDB1V3
H23	GND
H24	VCOMPLB
H25	GBC2/IO84PDB2V0
H26	IO84NDB2V0
H27	IO96PDB2V1
H28	IO96NDB2V1
H29	IO89PDB2V0
H30	IO89NDB2V0
J1	IO290NDB7V2
J2	IO290PDB7V2
J3	IO302NDB7V3
J4	IO302PDB7V3

Revision	Changes	Page
Revision 11 (August 2012)	Added a Note stating "VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information." to Table 2-1 • Absolute Maximum Ratings and Table 2-2 • Recommended Operating Conditions [1] (SAR 38322).	2-1 3-1 2-1
	The drive strength, IOL, and IOH value for 3.3 V GTL and 2.5 V GTL was changed from 25 mA to 20 mA in the following tables (SAR 31924): "Summary of Maximum and Minimum DC Input and Output Levels" table "Summary of I/O Timing Characteristics—Software Default Settings" table "I/O Output Buffer Maximum Resistances[1]" table "Minimum and Maximum DC Input and Output Levels" table) "Minimum and Maximum DC Input and Output Levels" table Also added note stating "Output drive strength is below JEDEC specification" for Tables 2-17 and 2-19. Additionally, the IOL and IOH values for 3.3 V GTL+ and 2.5 V GTL+ were corrected from 51 to 35 (for 3.3 V GTL+) and from 40 to 33 (for 2.5 V GTL+) in table Table 2-13 (SAR 39714).	 2-16 2-19 2-20 2-39 2-40
	"Duration of Short Circuit Event Before Failure" table was revised to change the maximum temperature from 110°C to 100°C, with an example of six months instead of three months (SAR 37934).	2-22
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 34796): "It uses a 5 V–tolerant input buffer and push-pull output buffer." This change was made in revision 10 and omitted from the change table in error.	2-30
Revision 11 (continued)	Figure 2-11 was updated to match tables in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section (SAR 34889).	2-38
	In Table 2-81 VIL and VIH were revised so that the maximum is 3.6 V for all listed values of VCCI (SAR 37222).	2-52
	Figure 2-47and Figure 2-48 are new (SAR 34848).	2-79
	The following sentence was removed from the "VMVx I/O Supply Voltage (quiet)" section in the "Pin Descriptions and Packaging" chapter: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with “Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks” (SAR 38322). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1

Revision	Changes	Page
Advance v0.3 (continued)	The "Methodology" section was updated.	3-9
	The A3PE3000 "208-Pin PQFP" pin table was updated.	4-6